L	Hits	Search Text	DB	Time stamp
Number				
2	64606	(thin near film near transistor) TFT OTFT	USPAT;	2004/08/27
			US-PGPUB;	14:11
	:		EPO; JPO;	
	İ	· ·	DERWENT;	
			IBM TDB	
4	283825	source and drain	USPĀT;	2004/08/27
			US-PGPUB;	14:51
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	74579	(first near2 (insulat\$3 dielectric)) and	USPAT;	2004/08/27
	'10'/5	(second near2 (insulat\$3 dielectric))	US-PGPUB;	14:52
		(Second Mediz (Insulacys dielectife))	EPO; JPO;	11.02
			DERWENT;	
			IBM TDB	
22	4730	((thin near film near transistor) TFT	USPAT:	2004/08/27
22	4/30	, ,		
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:53
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
	1	near2 (insulat\$3 dielectric)))	DERWENT;	
			IBM_TDB	
24	4110	(,,====== === ========================	USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:54
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
		near2 (insulat\$3 dielectric)))) and	DERWENT;	
		(@ad<20020923 @rlad<20020923)	IBM_TDB	
25	4071	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	14:54
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
		near2 (insulat\$3 dielectric)))) and	DERWENT;	
		(@ad<20020923 @rlad<20020923)) and gate	IBM TDB	
26	1889	((((thin near film near transistor) TFT	USPAT;	2004/08/27
	1	OTFT) and (source and drain) and ((first	US-PGPUB;	14:54
		near2 (insulat\$3 dielectric)) and (second	EPO; JPO;	
		near2 (insulat\$3 dielectric)))) and	DERWENT;	
		(@ad<20020923 @rlad<20020923)) and gate)	IBM TDB	
		and organic	<u>-</u>	i

L	Hits	Search Text	DB	Time stamp
Number				
2	64606	(thin near film near transistor) TFT OTFT	USPAT;	2004/08/27
			US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	283825	source and drain	USPAT;	2004/08/27
]			US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	2906	(first near gate near (insulat\$3	USPAT;	2004/08/27
i		dielectric)) and (second near gate near	US-PGPUB;	11:35
		(insulat\$3 dielectric))	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
6	476	, ,,,,	USPAT;	2004/08/27
		OTFT) and (source and drain) and ((first	US-PGPUB;	11:35
		near gate near (insulat\$3 dielectric))	EPO; JPO;	
		and (second near gate near (insulat\$3	DERWENT;	
L		dielectric)))	IBM_TDB	